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	Filing Date		2005-04-11	
	First Named Inventor	Sugawara		
	Art Unit	2826		
	Examiner Name	SEFER, AHMED N		
	Attorney Docket Number	3688KE-1		

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1	RYU ET AL., "3100 V, Asymmetrical, Gate Turn-Off (GTO) Thyristors in 4H-SiC", IEEE Electron Device Letters, Vol. 22, No. 3, March 2001, pages 127-129	<input type="checkbox"/>
2	RAHIMO ET AL., "Extending the Boundary Limits of High Voltage IGBTs and Diodes to above 8kV", Proceedings of the 14th International Symposium on Power Semiconductor Devices & ICs 2002, pages 41-44	<input type="checkbox"/>

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